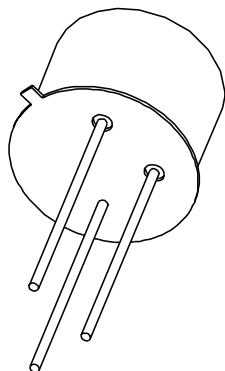


DATA SHEET



2N2219; 2N2219A NPN switching transistors

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 May 07

NPN switching transistors

2N2219; 2N2219A

FEATURES

- High current (max. 800 mA)
- Low voltage (max. 40 V).

APPLICATIONS

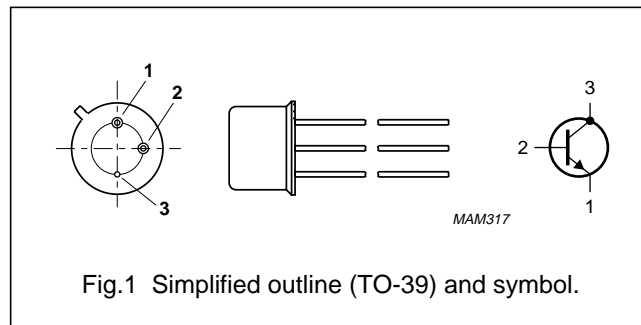
- High-speed switching
- DC and VHF/UHF amplification, for 2N2219 only.

DESCRIPTION

NPN switching transistor in a TO-39 metal package.
PNP complement: 2N2905A.

PINNING

| PIN | DESCRIPTION |
|-----|------------------------------|
| 1 | emitter |
| 2 | base |
| 3 | collector, connected to case |



QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|---------------------------|---|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | | | |
| | 2N2219 | | – | 60 | V |
| | 2N2219A | | – | 75 | V |
| V_{CEO} | collector-emitter voltage | open base | | | |
| | 2N2219 | | – | 30 | V |
| | 2N2219A | | – | 40 | V |
| I_C | collector current (DC) | | – | 800 | mA |
| P_{tot} | total power dissipation | $T_{amb} \leq 25\text{ }^\circ\text{C}$ | – | 800 | mW |
| h_{FE} | DC current gain | $I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$ | 75 | – | |
| f_T | transition frequency | $I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$ | | | |
| | 2N2219 | | 250 | – | MHz |
| | 2N2219A | | 300 | – | MHz |
| t_{off} | turn-off time | $I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA}; I_{Boff} = -15\text{ mA}$ | – | 250 | ns |

NPN switching transistors

2N2219; 2N2219A

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|--|------------------------------------|------|------|------|
| V _{CBO} | collector-base voltage 2N2219 2N2219A | open emitter | – | 60 | V |
| | | | – | 75 | V |
| V _{CEO} | collector-emitter voltage 2N2219 2N2219A | open base | – | 30 | V |
| | | open base; I _C ≤ 500 mA | – | 40 | V |
| V _{EBO} | emitter-base voltage 2N2219 2N2219A | open collector | – | 5 | V |
| | | | – | 6 | V |
| I _C | collector current (DC) | | – | 800 | mA |
| I _{CM} | peak collector current | | – | 800 | mA |
| I _{BM} | peak base current | | – | 200 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | – | 800 | mW |
| | | T _{case} ≤ 25 °C | – | 3 | W |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| T _j | junction temperature | | – | 200 | °C |
| T _{amb} | operating ambient temperature | | –65 | +150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|-------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | in free air | 190 | K/W |
| R _{th j-c} | thermal resistance from junction to case | | 50 | K/W |

NPN switching transistors

2N2219; 2N2219A

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-------------|---|--|------|------|---------------|
| I_{CBO} | collector cut-off current 2N2219 | $I_E = 0; V_{CB} = 50\text{ V}$ | – | 10 | nA |
| | | $I_E = 0; V_{CB} = 50\text{ V}; T_{amb} = 150\text{ °C}$ | – | 10 | μA |
| I_{CBO} | collector cut-off current 2N2219A | $I_E = 0; V_{CB} = 60\text{ V}$ | – | 10 | nA |
| | | $I_E = 0; V_{CB} = 60\text{ V}; T_{amb} = 150\text{ °C}$ | – | 10 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = 3\text{ V}$ | – | 10 | nA |
| h_{FE} | DC current gain | $I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V}$ | 35 | – | |
| h_{FE} | DC current gain | $I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$ | 50 | – | |
| h_{FE} | DC current gain | $I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$ | 75 | – | |
| h_{FE} | DC current gain 2N2219A | $I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; T_{amb} = -55\text{ °C}$ | 35 | – | |
| h_{FE} | DC current gain | $I_C = 150\text{ mA}; V_{CE} = 1\text{ V}; \text{note 1}$ | 50 | – | |
| h_{FE} | DC current gain | $I_C = 150\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$ | 100 | 300 | |
| h_{FE} | DC current gain 2N2219 2N2219A | $I_C = 500\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$ | 30 | – | |
| | | | 40 | – | |
| V_{CEsat} | collector-emitter saturation voltage 2N2219 2N2219A | $I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$ | – | 400 | mV |
| | | | – | 300 | mV |
| V_{CEsat} | collector-emitter saturation voltage 2N2219 2N2219A | $I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$ | – | 1.6 | V |
| | | | – | 1 | V |
| V_{BEsat} | base-emitter saturation voltage 2N2219 2N2219A | $I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$ | – | 1.3 | V |
| | | | 0.6 | 1.2 | V |
| V_{BEsat} | base-emitter saturation voltage 2N2219 2N2219A | $I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$ | – | 2.6 | V |
| | | | – | 2 | V |
| C_c | collector capacitance | $I_E = i_e = 0; V_{CB} = 10\text{ V}$ | – | 8 | pF |
| C_e | emitter capacitance 2N2219A | $I_C = i_c = 0; V_{EB} = 500\text{ mV}$ | – | 25 | pF |
| f_T | transition frequency 2N2219 2N2219A | $I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz};$ | 250 | – | MHz |
| | | | 300 | – | MHz |
| F | noise figure 2N2219A | $I_C = 0.2\text{ mA}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$ | – | 4 | dB |

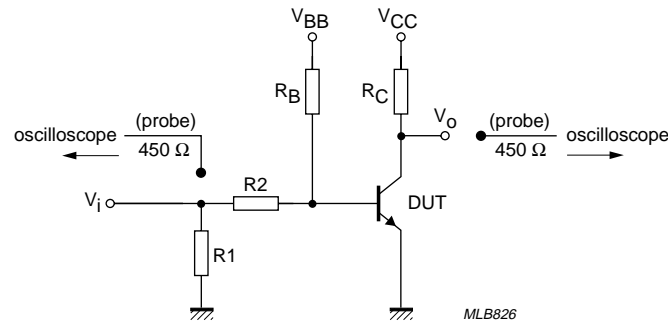
NPN switching transistors

2N2219; 2N2219A

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|---|---------------|---|------|------|------|
| Switching times (between 10% and 90% levels) for type 2N2219A; see Fig.2 | | | | | |
| t_{on} | turn-on time | $I_{Con} = 150 \text{ mA}; I_{Bon} = 15 \text{ mA};$ $I_{Boff} = -15 \text{ mA}$ | – | 35 | ns |
| t_d | delay time | | – | 15 | ns |
| t_r | rise time | | – | 20 | ns |
| t_{off} | turn-off time | | – | 250 | ns |
| t_s | storage time | | – | 200 | ns |
| t_f | fall time | | – | 60 | ns |

Note

1. Pulse test: $t_p \leq 300 \mu\text{s}; \delta \leq 0.02$.



$V_i = 9.5 \text{ V}; T = 500 \mu\text{s}; t_p = 10 \mu\text{s}; t_r = t_f \leq 3 \text{ ns}.$
 $R1 = 68 \Omega; R2 = 325 \Omega; R_B = 325 \Omega; R_C = 160 \Omega.$
 $V_{BB} = -3.5 \text{ V}; V_{CC} = 29.5 \text{ V}.$
 Oscilloscope: input impedance $Z_i = 50 \Omega.$

Fig.2 Test circuit for switching times.

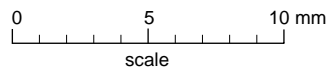
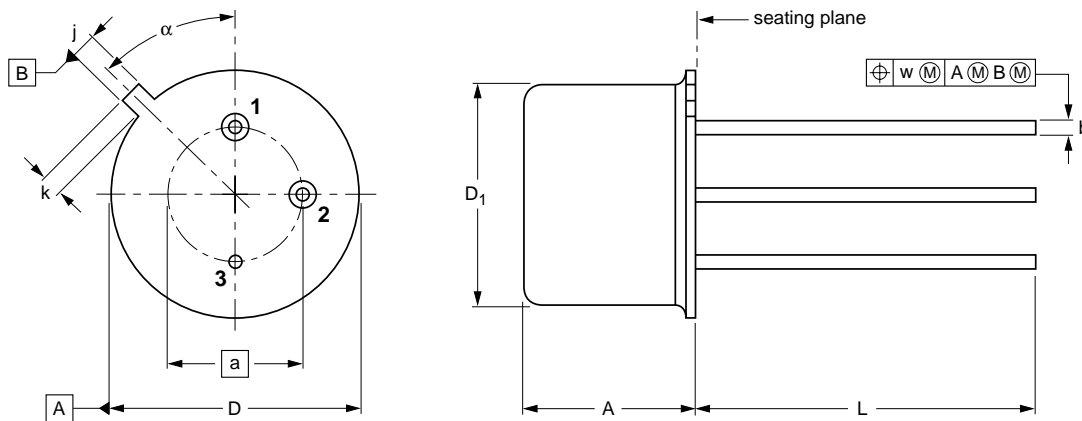
NPN switching transistors

2N2219; 2N2219A

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

| UNIT | A | a | b | D | D ₁ | j | k | L | w | α |
|------|--------------|------|--------------|--------------|----------------|--------------|--------------|--------------|-----|----------|
| mm | 6.60 6.35 | 5.08 | 0.48 0.41 | 9.39 9.08 | 8.33 8.18 | 0.85 0.75 | 0.95 0.75 | 14.2 12.7 | 0.2 | 45° |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|--|---------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT5/11 | | TO-39 | | | | 97-04-11 |

NPN switching transistors

2N2219; 2N2219A

DEFINITIONS

| Data sheet status | |
|---|---|
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 689 211, Fax. +359 2 689 102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,
Tel. +45 32 88 2636, Fax. +45 31 57 0044

Finland: Sinikallontie 3, FIN-02630 ESPOO,
Tel. +358 9 615800, Fax. +358 9 61580920

France: 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

Hungary: see Austria

India: Philips INDIA Ltd, Shivsagar Estate, A Block, Dr. Annie Besant Rd.
Worli, MUMBAI 400 018, Tel. +91 22 4938 541, Fax. +91 22 4938 722

Indonesia: see Singapore

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Ul. Lukiska 10, PL 04-123 WARSZAWA,
Tel. +48 22 612 2831, Fax. +48 22 612 2327

Portugal: see Spain

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Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231,
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South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,
Tel. +27 11 470 5911, Fax. +27 11 470 5494

South America: Rua do Rocio 220, 5th floor, Suite 51,
04552-903 São Paulo, SÃO PAULO - SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 829 1849

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 3 301 6312, Fax. +34 3 301 4107

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Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,
TAIPEI, Taiwan Tel. +886 2 2134 2865, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,
Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,
Tel. +90 212 279 2770, Fax. +90 212 282 6707

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381

Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,
Tel. +381 11 625 344, Fax. +381 11 635 777

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